

## 0.8 V to 2.5 V, 28 m $\Omega$ , Slew Rate Controlled Load Switch in WCSP4

### DESCRIPTION

The SiP32454 and SiP32455 are slew rate controlled integrated high side load switches that operate in the input voltage range from 0.8 V to 2.5 V. The SiP32454 and SiP32455 are of n-channel MOSFET switching elements that provide 28 m $\Omega$  switch on resistance. They have a 1 ms at 1.2 V and 1.5 ms at 2.5 V slow slew rate that limits the in-rush current and minimizes the switching noise. These devices' low voltage logic control threshold can interface with low voltage control I/O directly without extra level shift or driver. A 2 MW pull-down resistor is integrated at logic control EN pin. SiP32454 integrates a switch off output discharge circuit.

Both SiP32454 and SiP32455 are available in compact wafer level CSP package, WCSP4 0.8 mm x 0.8 mm with 0.4 mm pitch.

TYPICAL APPLICATION CIRCUIT

### FEATURES

- Low input voltage, 0.8 V to 2.5 V
- Low R<sub>ON</sub>, 28 mΩ typical
- Slew rate control
- · Low logic control with hysteresis
- Reverse current blocking when disabled
- Integrated output discharge switch for SiP32454
- Integrated pull down resistor at EN pin
- 4 bump WCSP 0.8 mm x 0.8 mm with 0.4 mm pitch package
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

### APPLICATIONS

- Battery operated devices
- Smart phones
- GPS and PMP
- Computer
- Medical and healthcare equipment
- Industrial and instrument
- Cellular phones and portable media players
- Game consol

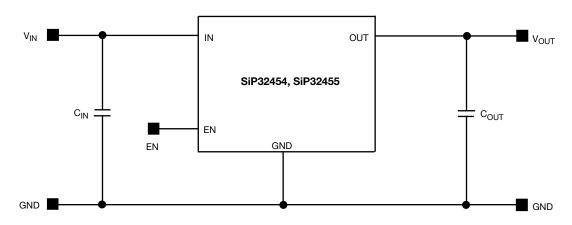


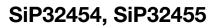
Fig. 1 - SiP32454 and SiP32455 Typical Application Circuit

ORDERING INFORMATION						
TEMPERATURE RANGE	PACKAGE	MARKING	PART NUMBER			
-40 °C to +85 °C	WCSP: 4 bumps (2 x 2, 0.4 mm pitch, 208 µm bump height, 0.8 mm x 0.8 mm die size)	AD	SiP32454DB-T2-GE1			
		AE	SiP32455DB-T2-GE1			

Note

-GE1 denotes halogen-free and RoHS-compliant

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ABSOLUTE MAXIMUM RATINGS						
PARAMETER	LIMIT	UNIT				
Supply input voltage (VIN)	-0.3 to 2.75					
Enable input voltage (V <sub>EN</sub> )	-0.3 to 2.75	V				
Output voltage (V <sub>OUT</sub> )	-0.3 to 2.75					
Maximum continuous switch current (I <sub>max.</sub> )	1.2	٨				
Maximum repetitive pulsed current (I_DM) $V_{\rm IN}$ (pulsed at 1 ms, 10 % duty cycle)	2	- A				
ESD rating (HBM)	4000	V				
Junction temperature (T <sub>J</sub> )	-40 to +150	°C				
Thermal resistance (θ <sub>JA</sub> ) <sup>a</sup>	280	°C/W				
Power dissipation (P <sub>D</sub> ) <sup>a</sup>	196	mW				

Notes

a. Device mounted with all leads and power pad soldered or welded to PC board, see PCB layout

b. Derate 3.6 mW/°C above  $T_A = 25$  °C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating/conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING RANGE						
PARAMETER	LIMIT	UNIT				
Input voltage range (V <sub>IN</sub> )	0.8 to 2.5	V				
Operating junction temperature range (T <sub>J</sub> )	-40 to +125	°C				

	1 1	TEST CONDITIONS	UNLESS SPECIFIED		LIMITS		1	
PARAMETER	SYMBOL	$V_{IN} = 1 \text{ V}, \text{ T}_{A} = -40 \text{ °C to } +85 \text{ °C}$ (typical values are at $\text{T}_{A} = 25 \text{ °C}$ )		MIN. <sup>a</sup> TYP. <sup>b</sup>		MAX. a	UNIT	
Operating voltage <sup>c</sup>	V <sub>IN</sub>		0.8	-	2.5	V		
Quiescent current	I <sub>Q</sub> -	$V_{IN}$ = 1.2 V, $V_{EN}$ = $V_{IN}$ , OUT = open		-	10	15		
Quescent current		$V_{IN} = 2.5 V, V_{EN}$	= V <sub>IN</sub> , OUT = open	-	34	60	-μΑ	
Off annual command		SiP32454		-	-	30		
Off supply current	I <sub>Q(off)</sub>	SiP32455	EN = GND, OUT = open	-	-	1		
Off switch current	I <sub>DS(off)</sub>	EN = GND	0, OUT = 0 V	-	-	30		
Reverse blocking current	I <sub>RB</sub>	V <sub>OUT</sub> = 2.5 V, V <sub>IN</sub>	<sub>N</sub> = 0.9 V, V <sub>EN</sub> = 0 V	-	0.001	30	1	
		$V_{IN} = 1 \text{ V}, I_{L} = 200 \text{ mA}, T_{A} = 25 \text{ °C}$		-	30	35	- mΩ	
		$V_{IN} = 1.2 \text{ V}, I_L = 2$	-	29	35			
On-resistance	R <sub>DS(on)</sub>	V <sub>IN</sub> = 1.8 V, I <sub>L</sub> = 200 mA, T <sub>A</sub> = 25 °C		-	28	35		
		$V_{IN} = 2.5 V, I_{L} = 2$	-	28	35			
On-resistance temp. coefficient	TC <sub>RDS</sub>			-	4100	-	ppm/°	
Output pull-down resistance	R <sub>PD</sub>	$V_{EN} = 0 V, T_A = 25$	5 °C (SiP32454 only)	-	417	550	Ω	
EN input low voltage <sup>c</sup>	V <sub>IL</sub>	V <sub>IN</sub>	= 1 V	-	-	0.1	v	
EN input high voltage <sup>c</sup>	V <sub>IH</sub>	V <sub>IN</sub> =	= 2.5 V	1.5	-	-	v	
	I <sub>EN</sub>	V <sub>IN</sub> = 2.5 V, V <sub>EN</sub> = 0 V		-	-	1		
EN input leakage		V <sub>IN</sub> = 2.5 V, V <sub>EN</sub> = 2.5 V		-	6.5	12	μA	
	t <sub>d(on)</sub>	V <sub>IN</sub> = 1.2 V		-	0.6	1.2	ms	
Output turn-on delay time		V <sub>IN</sub> = 2.5 V		-	0.6	1.2		
Output turn-on rise time	t <sub>r</sub> -	V <sub>IN</sub> = 1.2 V	$R_{I,OAD} = 10 \Omega$ ,	0.4	1	1.6		
		V <sub>IN</sub> = 2.5 V	$C_L = 0.1 \ \mu F$ , $T_A = 25 \ ^{\circ}C$	0.5	1.5	2.5	1	
		V <sub>IN</sub> = 1.2 V		-	0.3	1	μs	
Output turn-off delay time	t <sub>d(off)</sub>	V <sub>IN</sub> = 2.5 V	1	-	0.1	1		

#### Notes

a. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum
b. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing
c. For V<sub>IN</sub> outside this range consult typical EN threshold curve

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### **PIN CONFIGURATION**

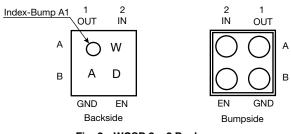
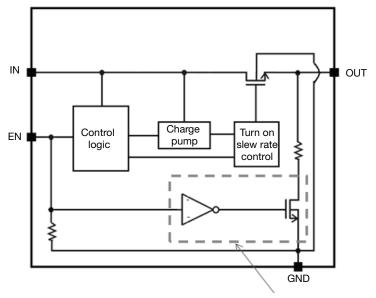


Fig. 2 - WCSP 2 x 2 Package

PIN DESCRIPTION					
PIN NUMBER	NAME	FUNCTION			
A1	OUT	This is the output pin of the switch			
A2	IN	This is the input pin of the switch			
B1	GND	Ground connection			
B2	EN	Enable input			

### **BLOCK DIAGRAM**

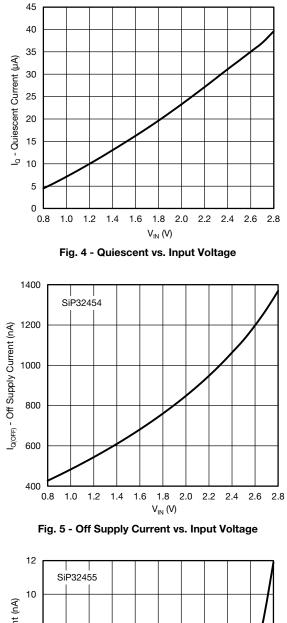


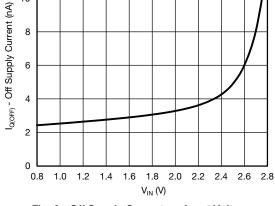
For SiP32454 only

Fig. 3 - Functional Block Diagram



## TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)







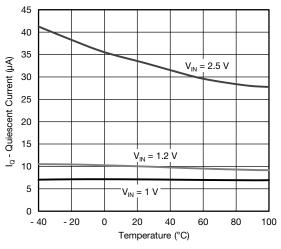


Fig. 7 - Quiescent vs. Temperature

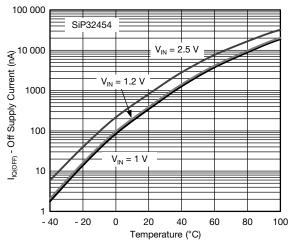
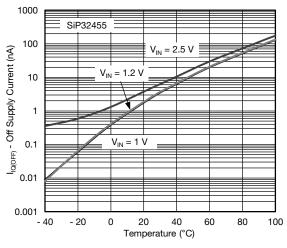


Fig. 8 - Off Supply Current vs. Temperature





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## TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

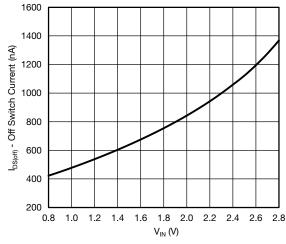


Fig. 10 - Off Switch Current vs. Input Voltage

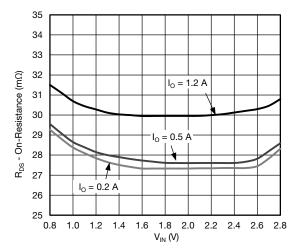


Fig. 11 - On Resistance vs. Input Voltage

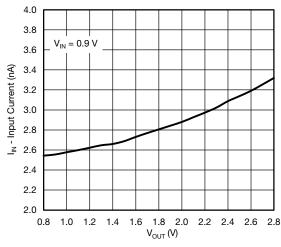


Fig. 12 - Reverse Blocking Current vs. Output Voltage

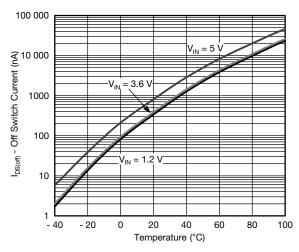


Fig. 13 - Off Switch Current vs. Temperature

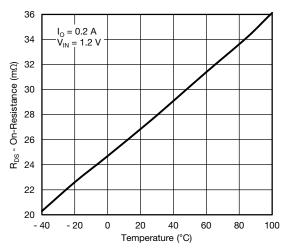
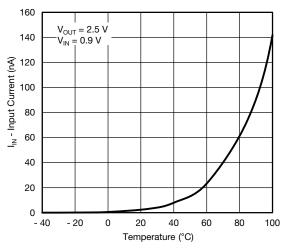
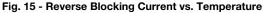


Fig. 14 - On Resistance vs. Temperature





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## SiP32454, SiP32455



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## TYPICAL CHARACTERISTICS (internally regulated, 25 °C, unless otherwise noted)

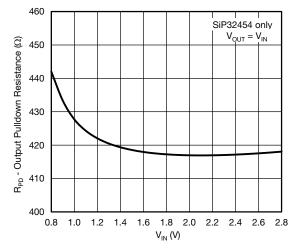


Fig. 16 - Output Pull-Down Resistance vs. Input Voltage

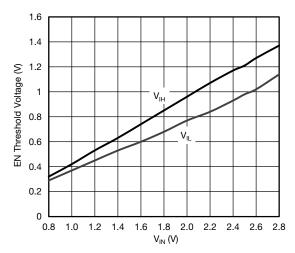


Fig. 17 - EN Threshold Voltage vs. Input Voltage

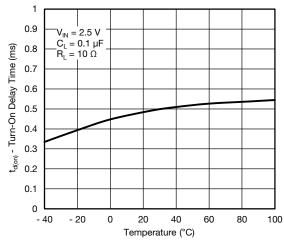


Fig. 18 - Turn-On Delay Time vs. Temperature

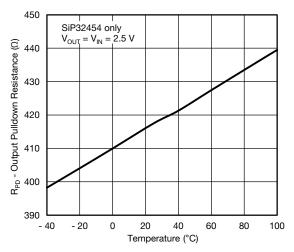


Fig. 19 - Output Pull-Down Resistance vs. Temperature

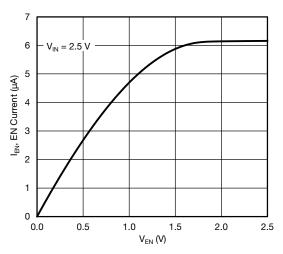


Fig. 20 - EN Input Leakage vs. V<sub>EN</sub>

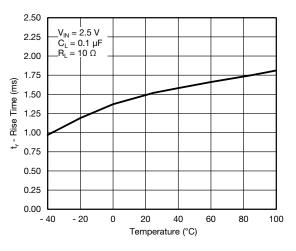


Fig. 21 - Rise Time vs. Temperature

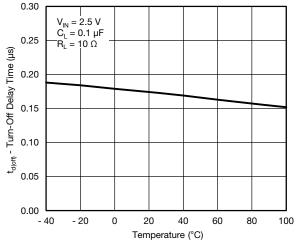
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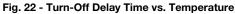
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### **ELECTRICAL CHARACTERISTICS**





### **TYPICAL WAVEFORMS**

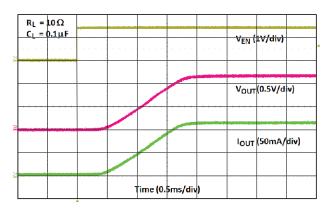


Fig. 23 - Turn-On Time (V<sub>IN</sub> = 1.2 V)

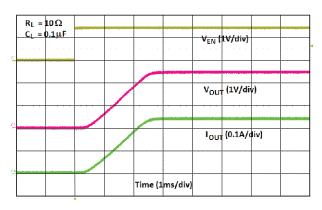


Fig. 24 - Turn-On Time (V<sub>IN</sub> = 2.5 V)

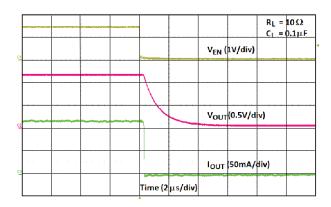


Fig. 25 - Turn-Off Time (V<sub>IN</sub> = 1.2 V)

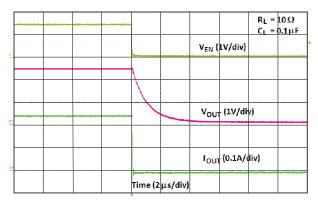


Fig. 26 - Turn-Off Time (V<sub>IN</sub> = 2.5 V)

#### **DETAILED DESCRIPTION**

SiP32454 and SiP32455 are n-channel power MOSFET designed as high side load switch. Once enable the device charge pumps the gate of the power MOSFET to a constant gate to source voltage for fast turn on time. The mostly constant gate to source voltage keeps the on resistance low through out the input voltage range. SiP32454 and SiP32455 are designed with slow slew rate to minimize the inrush current during turn on. Because the body of the output n-channel is always connected to GND, it prevents the current from going back to the input in case the output voltage is higher than the output. The SiP32454 especially incorporates an active output pull-down resistor to discharge output capacitance when the device is off.

#### **APPLICATION INFORMATION**

#### Input Capacitor

While a bypass capacitor on the input is not required, a 4.7  $\mu$ F or larger capacitor for C<sub>IN</sub> is recommended in almost all applications. The bypass capacitor should be placed as physically close as possible to the input pin to be effective in minimizing transients on the input. Ceramic capacitors are recommended over tantalum because of their ability to withstand input current surges from low impedance sources such as batteries in portable devices.

#### **Output Capacitor**

A 0.1  $\mu$ F capacitor across V<sub>OUT</sub> and GND is recommended to insure proper slew operation. There is inrush current through the output MOSFET and the magnitude of the inrush current depends on the output capacitor, the bigger the C<sub>OUT</sub> the higher the inrush current. There are no ESR or capacitor type requirement.

#### Enable

The EN pin is compatible with CMOS logic voltage levels. It requires at least 0.1 V or below to fully shut down the device and 1.5 V or above to fully turn on the device.

#### **Protection Against Reverse Voltage Condition**

Both the SiP32454 and SiP32455 can block the output current from going to the input in case where the output voltage is higher than the input voltage when the main switch is off.

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#### Thermal Considerations

These devices are designed to maintain a constant output load current. Due to physical limitations of the layout and assembly of the device the maximum switch current is 1.2 A as stated in the Absolute Maximum Ratings table. However, another limiting characteristic for the safe operating load current is the thermal power dissipation of the package. To obtain the highest power dissipation (and a thermal resistance of 280 °C/W) the device should be connected to a heat sink on the printed circuit board.

The maximum power dissipation in any application is dependent on the maximum junction temperature,  $T_{J(max.)} = 125$  °C, the junction-to-ambient thermal resistance,  $\theta_{JA} = 280$  °C/W, and the ambient temperature,  $T_A$ , which may be formulaically expressed as:

P (max.) = 
$$\frac{T_{J(max.)} - T_A}{\theta_{JA}} = \frac{125 - T_A}{280}$$

It then follows that, assuming an ambient temperature of 70  $^{\circ}$ C, the maximum power dissipation will be limited to about 196 mW.

So long as the load current is below the 1.2 A limit, the maximum continuous switch current becomes a function two things: the package power dissipation and the  $R_{DS(on)}$  at the ambient temperature.

As an example let us calculate the worst case maximum load current at  $T_A = 70$  °C. The worst case  $R_{DS(on)}$  at 25 °C is 35 m $\Omega$ . The  $R_{DS(on)}$  at 70 °C can be extrapolated from this data using the following formula:

 $R_{DS(on)}$  (at 70 °C) =  $R_{DS(on)}$  (at 25 °C) x (1 +  $T_C$  x  $\Delta T$ )

Where  $T_C$  is 4100 ppm/°C. Continuing with the calculation we have

 $R_{DS(on)}$  (at 70 °C) = 35 m $\Omega$  x (1 + 0.0041 x (70 °C - 25 °C)) = 42.2 m $\Omega$ 

The maximum current limit is then determined by

$$I_{LOAD(max.)} < \sqrt{\frac{P(max.)}{R_{DS(on)}}}$$

which in this case is 2.1 A. Under the stated input voltage condition, if the 2.1 A current limit is exceeded the internal die temperature will rise and eventually, possibly damage the device.

To avoid possible permanent damage to the device and keep a reasonable design margin, it is recommended to operate the device maximum up to 1.2 A only as listed in the Absolute Maximum Ratings table.

## SiP32454, SiP32455



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PRODUCT SUMMARY			
Part number	SiP32454	SiP32455	
Description	0.8 V to 2.5 V, 28 m $\Omega$ , 1.5 ms rise time, output discharge	0.8 V to 2.5 V, 28 m $\Omega$ , 1.5 ms rise time	
Configuration	Single	Single	
Slew rate time (µs)	1000	1000	
On delay time (μs)	600	600	
Input voltage min. (V)	0.8	0.8	
Input voltage max. (V)	2.5	2.5	
On-resistance at input voltage min. (m $\Omega$ )	30	30	
On-resistance at input voltage max. (m $\Omega$ )	28	28	
Quiescent current at input voltage min. (µA)	4	4	
Quiescent current at input voltage max. (µA)	32	32	
Output discharge (yes / no)	Yes	No	
Reverse blocking (yes / no)	Yes	Yes	
Continuous current (A)	1.2	1.2	
Package type	WCSP4	WCSP4	
Package size (W, L, H) (mm)	0.8 x 0.8 x 0.5	0.8 x 0.8 x 0.5	
Status code	2	2	
Product type	Slew rate	Slew rate	
Applications	Computers, consumer, industrial, healthcare, networking, portable	Computers, consumer, industrial, healthcare, networking, portable	

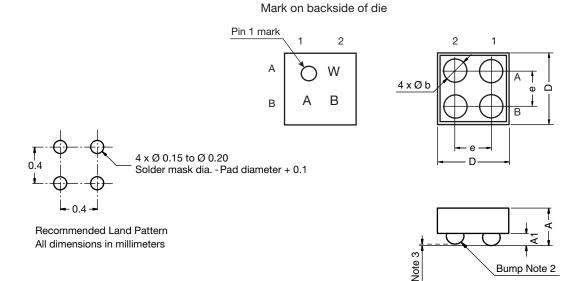
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## WCSP4: 4 Bumps

(2 x 2, 0.4 mm pitch, 208 µm bump height, 0.8 mm x 0.8 mm die size)



DWG-No: 6004

#### Notes

<sup>(1)</sup> Laser mark on the backside surface of die

(2) Bumps are SAC396

<sup>(3)</sup> 0.05 max. coplanarity

DIM.		MILLIMETERS <sup>a</sup>		INCHES			
DIN.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
A	0.515	0.530	0.545	0.0203	0.0209	0.0215	
A1	0.208			0.0082			
b	0.250 0.260 0.270		0.270	0.0098	0.0102	0.0106	
e	0.400			e 0.400 0.0157			
D	0.720	0.760	0.800	0.0283	0.0299	0.0315	

Note

a. Use millimeters as the primary measurement



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